

BD235 BD236 BD237 BD238

COMPLEMENTARY SILICON POWER TRANSISTORS

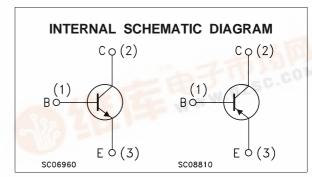
 STMicroelectronics PREFERRED SALESTYPES

DESCRIPTION

The BD235 and BD237 are silicon epitaxial-base NPN power transistors in Jedec SOT-32 plastic package inteded for use in medium power linear and switching applications.

The complementary PNP types are BD236 and BD238 respectively.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Va	Unit	
		NPN	BD235	BD237	POY
		PNP	BD236	BD238	50.C.
V _{CBO}	Collector-Base Voltage (I _E = 0)		60	100	V
Vcer	Collector-Base Voltage (R _{BE} = 1KΩ)		60	100	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		60	80	V
V_{EBO}	Emitter-Base Voltage (I _C = 0)		5		V
Ic	Collector Current		2		Α
Ісм	Collector Peak Current (tp < 5 ms)		6		А
Ptot	Total Dissipation at T _c = 25 °C		25		W
T _{stg}	Storage Temperature		-65 to 150		°C
Tj	Max. Operating Junction Temperature		150		°C

For PNP types voltage and current values are negative.



BD235 BD236 BD237 BD238

THERMAL DATA

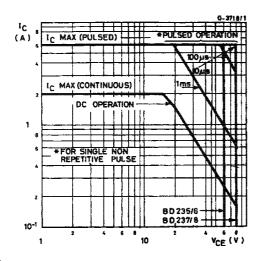
R _{thj-case} Thermal Resistance Junction-case	Max	5	°C/W	
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ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

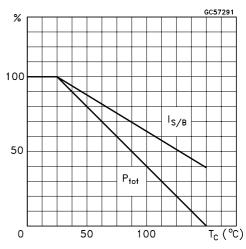
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V_{CE} = rated V_{CEO} V_{CE} = rated V_{CEO} T_c = 150 $^{\circ}$ C			0.1	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA for BD235 / BD236 for BD237 / BD238	60 80			V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 1 A I _B = 0.1 A			0.6	V
$V_{BE}*$	Base-Emitter Voltage	$I_C = 1 A$ $V_{CE} = 2 V$			1.3	V
h _{FE} *	DC Current Gain	$I_{C} = 150 \text{ mA}$ $V_{CE} = 2 \text{ V}$ $I_{C} = 1 \text{ A}$ $V_{CE} = 2 \text{ V}$	40 25			
f _T	Transition frequency	I _C = 250 mA	3			MHz
hFE1/hFE2*	Matched Pairs	Ic = 150 mA		1.6		

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

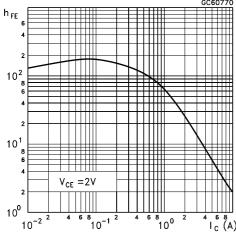
Safe Operating Area



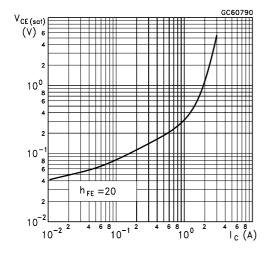
Derating Curve



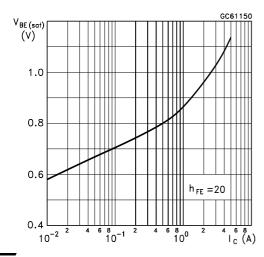
DC Current Gain (NPN type)



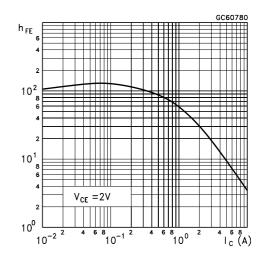
Collector-Emitter Saturation Voltage (NPN type)



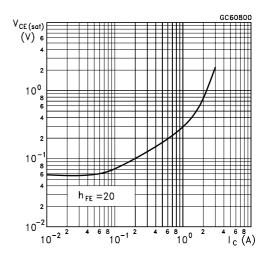
Base-Emitter Saturation Voltage (NPN type)



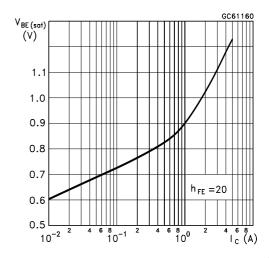
DC Current Gain (PNP type)



Collector-Emitter Saturation Voltage (PNP type)

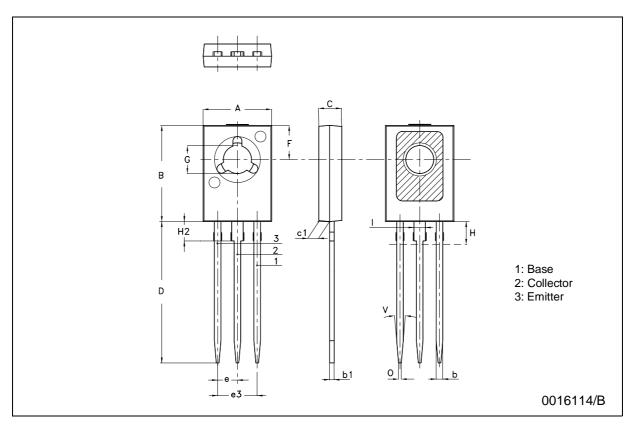


Collector-Base Capacitance (PNP type)



SOT-32 (TO-126) MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	7.4		7.8	0.291		0.307	
В	10.5		10.8	0.413		0.425	
b	0.7		0.9	0.028		0.035	
b1	0.40		0.65	0.015		0.025	
С	2.4		2.7	0.094		0.106	
c1	1.0		1.3	0.039		0.051	
D	15.4		16.0	0.606		0.630	
е		2.2			0.087		
e3		4.4			0.173		
F		3.8			0.150		
G	3		3.2	0.118		0.126	
Н			2.54			0.100	
H2		2.15			0.084		
I		1.27			0.05		
0		0.3			0.011		
V		10°			10°		



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